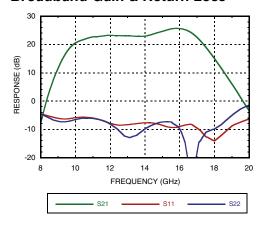


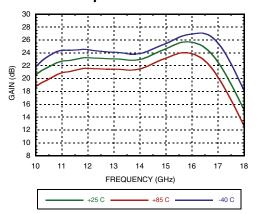


GaAs pHEMT MMIC LOW NOISE HIGH IP3 AMPLIFIER, 12 - 16 GHz

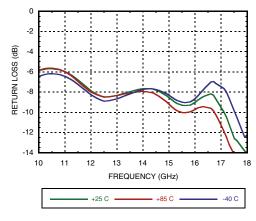
Broadband Gain & Return Loss



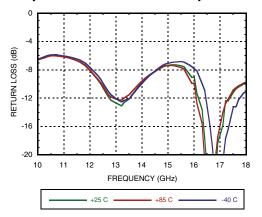
Gain vs. Temperature



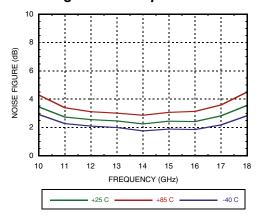
Input Return Loss vs. Temperature



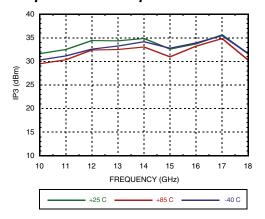
Output Return Loss vs. Temperature



Noise Figure vs. Temperature



Output IP3 vs. Temperature



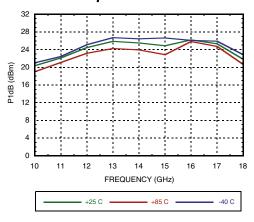
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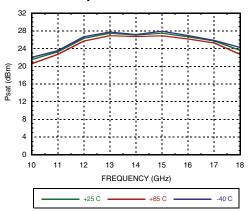


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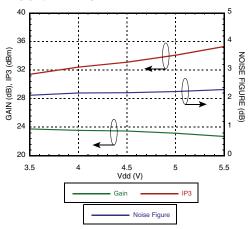
P1dB vs. Temperature



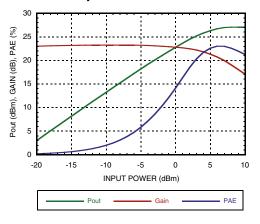
Psat vs. Temperature



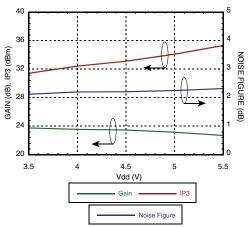
Gain, Noise Figure & OIP3 vs. Supply Voltage @ 14 GHz, Idd= 200 mA



Power Compression @ 14 GHz

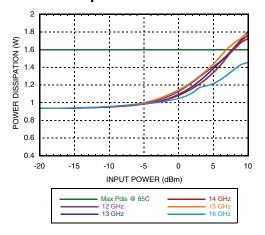


Gain, Noise Figure & IP3 vs. Supply Current @ 14 GHz, Vdd= 5V*



* Idd is controlled by varying Vgg

Power Dissipation



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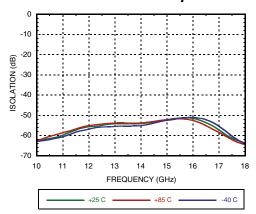
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GaAs pHEMT MMIC LOW NOISE HIGH IP3 AMPLIFIER, 12 - 16 GHz

Reverse Isolation vs. Temperature



Absolute Maximum Ratings

Duniu Dina Valtana (Valda Valda Valda)	. 5 5)/	
Drain Bias Voltage (Vdd1, Vdd2, Vdd3)	+5.5V	
Gate Bias Voltage (Vgg)	-4 to 0V	
RF Input Power (RFIN)(Vdd = +5V)	+10 dBm	
Channel Temperature	175 °C	
Continuous Pdiss (T = 85 °C)	1.6 W	
(derate 17.9 mW/°C above 85 °C)	1.0 VV	
Thermal Resistance (channel to ground paddle)	56 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	

ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Typical Supply Current vs. Vdd

Vdd (V)	ldd (mA)
+3.0	140
+3.5	154
+4.0	168
+4.5	188
+5.0	200
+5.5	208

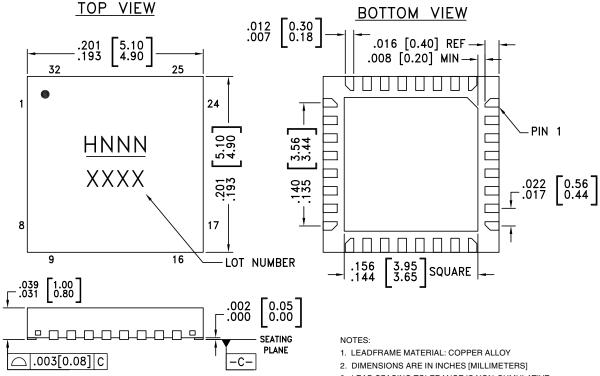
Note: Amplifier will operate over full voltage ranges shown above.





GaAs pHEMT MMIC LOW NOISE HIGH IP3 AMPLIFIER, 12 - 16 GHz

Outline Drawing



- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM. PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5 PACKAGE WARP SHALL NOT EXCEED 0.05mm
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC490LP5	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H490 XXXX
HMC490LP5E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H490 XXXX

- [1] Max peak reflow temperature of 235 °C
- [2] Max peak reflow temperature of 260 °C
- [3] 4-Digit lot number XXXX



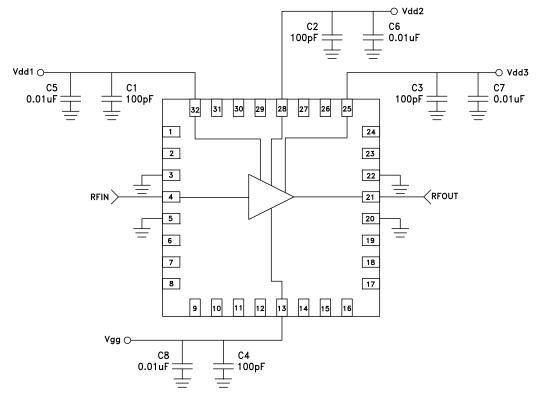


GaAs pHEMT MMIC LOW NOISE HIGH IP3 AMPLIFIER, 12 - 16 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 6 - 12, 14 - 19, 23, 24, 26, 27, 29 - 31	N/C	The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
3, 5, 20, 22	GND	Package bottom must also be connected to RF/DC ground.	GND =
4	RFIN	This pad is AC coupled and matched to 50 Ohms.	RFIN 0
13	Vgg	Gate control for amplifier. Adjust to achieve Idd of 200 mA. Please follow "MMIC Amplifier Biasing Procedure" Application Note. External bypass capacitors of 100 pF and 0.01 µF are required.	Vgg
21	RFOUT	This pad is AC coupled and matched to 50 Ohms.	—
25, 28, 32	Vdd3, 2, 1	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF and 0.01 μF are required.	

Application Circuit



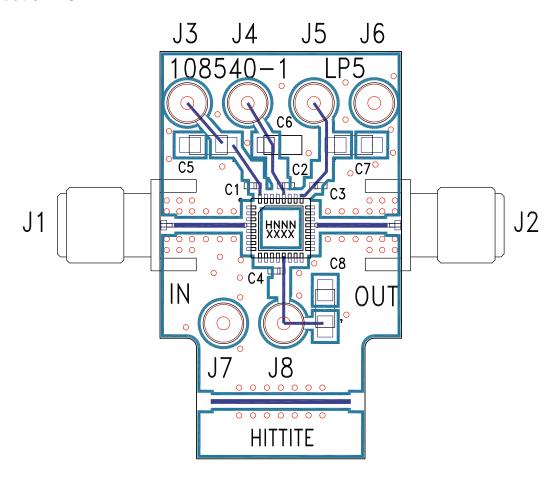
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GaAs pHEMT MMIC LOW NOISE HIGH IP3 AMPLIFIER, 12 - 16 GHz

Evaluation PCB



List of Materials for Evaluation PCB 108402 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3 - J8	DC Pin
C1 - C4	1000 pF Capacitor, 0402 Pkg.
C5 - C8	4.7 μF Capacitor, Tantalum
U1	HMC490LP5 / HMC490LP5E
PCB [2]	108540 Evaluation PCB

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

^[2] Circuit Board Material: Rogers 4350



HMC490LP5 / 490LP5E

v04.0213



GaAs pHEMT MMIC LOW NOISE HIGH IP3 AMPLIFIER, 12 - 16 GHz

Notes: